

Spin in semiconductor nanostructures

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Spin coherence of carriers in semiconductor quantum wells and quantum dots



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- Introduction to carrier spin coherence
- Experimental techniques
- Spin coherence in quantum wells
- Spin coherence in quantum dots
- Mode-locking of spin coherences

Motivation: Spin as a qu-bit

- classical information \Rightarrow bit: 0 or 1
- quantum information \Rightarrow quantum bit or 'qubit':

0, 1 or superposition

good candidate for 'qubit' is electron spin



Goals:

- creation of spin
- readout of spin
- control of spin

Loss and DiVincenzo PRA 57, 120 (1998)

electron spin in magnetic field





Optical orientation of carrier spin



 \Rightarrow electron spin is defined by laser polarization

Spin relaxation times







- T₁ is the time it takes for longitudinal spin polarization to reach equilibrium; relaxation process requires energy transfer
- T₂ decoherence is a result of a loss of the phase relation between the two eigenstates; no energy transfer, no change in occupation (T₂^{*} is defined for ensemble)

Dephasing of spin ensemble

Lamor spin precession in magnetic field



$$\omega_L = \frac{\mu_B g B}{\hbar}$$

frequency dispersion

$$\Delta \omega_L = \frac{\mu_B \, \Delta g \, B}{\hbar}$$

Ensemble looses spin synhronisation much faster than

the coherence is lost by individual spins: $T_2^* << T_2$

Detection of spin dynamics







Detection of spin dynamics







Spin coherence in InGaAs/GaAs QWs



with increasing of B:

increase of frequency



Spin coherence in InGaAs/GaAs QWs



• $T_2^* > 8 \text{ ns}$



Spin coherence in quantum wells

- Regime of diluted carrier gas
- Radiative times of excitons and trions
- Long electron spin coherence
- Generation mechanism of spin coherence for resonant excitation of trions
- Spin coherence of holes



Important role of Coulombic interaction !

Let's study materials with strong Coulombic interactions \rightarrow II-VI (CdTe, ZnSe, ZnO....)

II-VI QWs with strong Coulomb interaction



CdTe/CdMgTe quantum wells 200 Å QWs, 5 periods $n_e = 5 - 8 \times 10^9 \text{ cm}^{-2}$



Low-dense electron gas, charged exciton, TRION



Kinetics of exciton and trion photoluminescence



Excitation 1.5-ps pulses, detection with streak-camera



Fast decay of 20 ps is exciton radiative time.

Longer decay of 100 ps is due to exciton relaxation into radiative cone.



Pump-probe Kerr rotation with ps-pulses



S.A.Crooker, D.D. Awschalom, N. Samarth IEEE J. Quantum Electronic 1, 1082 (1995)

Resonant excitation in trion







Above-barrier illumination increases 2DEG concentration.

Beat frequency corresponds to electron Zeeman splitting with $g_e = |1.64|$.



Electron spin beats



200 Å MQW CdTe/(Cd,Mg)Te $n_e = 5 \times 10^9 \text{ cm}^{-2}$



Trion / exciton lifetime <100 ps

Spin beats come from 2DEG

Dephasing of spin coherence in magnetic fields



Decay of spin beats in B > 0.5 T is due to dephasing of ensemble T_{inh} . Single spin decoherence time $T_2 = 10$ ns is seen for B < 0.5 T.

Long-lived electron spin coherence





Period between pump puses 13.2 ns (repetition rate 75.6 MHz)

Electron spin coherence lives longer than 13.2 ns.

Other techniques are needed to measure spin coherence time:

Resonant Spin Amplification (RSA) technique.

Kikkawa and Awschalom, PRL 80, 4313 (1998).

Resonant Spin Amplification (RSA) technique





Very long electron spin coherence time T₂*=30 ns !!!

10 ns, GaAs QW, Dzhioev PRB 66 (2002). 300 ns, GaAs bulk, Dzhioev PRB 66 (2002). T = 1.6 - 5 K $B \rightarrow 0 \text{ T}$

Spin relaxation time vs pump power





Electron spin relaxation time depends on excitation power. Electron delocalization due to heating.

Spin coherence time vs bath temperature





Dyakonov-Perel relaxation of electrons in QWs for T > 10 K.

$$\frac{1}{\tau_s} \propto T \times \tau_p(T)$$

At T < 10 K fluctuations of nuclei field contribute to spin relaxation of localized electrons.







Problem: How the spin coherence is excited in low density 2DEG?

Free electrons of 2DEG with infinite lifetime.

Electrons in excitons. - Beat decay is limited by exciton lifetime of 30-100 ps.

Electrons in trions. – Trion has singlet state with two antiprallel electron spins and S=0. No spin precession is possible.



Conclusion: Long-lived beats can be from 2DEG only.

Problem: How the spin coherence in 2DEG is excited?

Mechanism of generation spin coherence in 2DEG via formation of trions



Degenerate pump-probe





Two-color pump-probe





Hole spin relaxation







Spin coherence of 2DEG is generated via trion formation when trions or excitons are excited resonantly.

Long-lived electron spin coherence in CdTe QWs:

 T_2^* = 30 ns, which means that T_2 > 30 ns.

Electron localization favors long spin coherence.

Spin coherence in InGaAs/GaAs QW



- Literature: $T_2^* = 10$ ns, GaAs QW
- T_2^* = 25 ns, GaAs QW
- T_2^* = 42 ns, InGaAs QW

Spin coherence in III-V QWs





- no alloy fluctuations
- shorter T₂*

- alloy fluctuations
- \Rightarrow in plane electron localization

Spin coherence of holes



p-doped GaAs/AlGaAs quantum well





Carrier concentration is tuned by above-barrier illumination.

p-type can be converted to n-type

Spin coherence of holes



p-doped GaAs/AlGaAs quantum well



Spin dephasing time of holes T_2^* is longer than 650 ps.

p-doped GaAs/AlGaAs quantum well



Similar to electrons localization favors long spin dephasing time for holes.



Spin coherence in quantum dots

- Singly charged InGaAs quantum dots
- Spin beats of resident electrons
- Generation mechanism of spin coherence for resonant excitation of trions

Self-organized quantum dots





- InGaAs / GaAs quantum dots (QDs)
- strong localization



InGaAs quantum dots



Ensemble of singly charged QDs



- 20 layers InGaAs/GaAs QDs
- dot density 10¹⁰ cm⁻²
- n-doped with dopant density ~ dot density

Resonant excitation of singly-charged dots



Charged exciton or "trion"



Optical generation of spin coherence

10.0 nm



Greilich et al. PRL 96, 227401 (2006)

Electron g-factor in quantum dots





In-plane anisotropy

Optical generation of spin coherence





InGaAs quantum dots





Pump power dependence



non-monotonic increase of amplitude with increasing excitation power

Rabi-oscillations

pulse area

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$$\theta = \frac{1}{\hbar} \int_{-\infty}^{\infty} \vec{p} \vec{E} dt$$







Generation of spin coherence



coherent spin superposition of electron and trion



Shabaev, Efros PRB 68, 201305R (2003) Greilich et al. PRL 96, 227401 (2006)





Spontaneous decay of trion does not affect spin coherence at $\omega_{I} \tau_{r} >> 1$

initialization of spin coherence



after a dozen of π-pulses: 99% electron spin polarization



Mode-locking of electron spin coherence

- Phase synchronization of spin precession
- Spin coherence time T_2 of electron in a dot
- Two-pulse control
- Robustness
- Polarization phase control

Spin precession at negative time delay



spin coherence in each dot lasts much longer than the pulse repetition period and dephasing time of ensemble ($T_2^*=2$ ns).

Greilich et al., Science 313, 341 (2006)

Spin coherence in QDs





- spin coherence of ensemble is short, $T_2^* < 10$ ns
- \Rightarrow spin coherence in each dot is longer than T_{rep}



Phase-locked spin precession

spin precession synchronized by mode-locked pump laser

Out of phase mode



time



Phase synchronization condition





Phase-locked spin precession







Phase synchronization condition



Spin coherence in QDs





Spin coherence time T₂ of single electron



Repetition period T_R varied by pulse-picker from 13 to 1000 ns



decay time is single dot coherence time $T_2 = 3 \ \mu s$

four orders of magnitude longer than ensemble dephasing $T_2^* = 0.4$ ns !

Petta et al., Science 309, 2180 (2005)

















Commensurability conditions:

 $T_D = T_R / 7 = 1.84 \text{ ns}$ $T_D = T_R / 4 = 3.26 \text{ ns}$ $T_D = T_R / 3 = 4.26 \text{ ns}$

Greilich et al., PRB 75, 233301 (2007)

Temperature stability of mode-locking





Robustness against magnetic field





Phase control of spin precession



Greilich et al., PRB 75, 233301 (2007)



Robustness of mode-locking:

- Wide range of Larmor frequencies, i.e. versus magnetic field
- Temperature range up to 40 K
- Ensemble of QDs with dispersion in energy and g-factor
- Spectrally broad laser line for generation and read out (1 meV)

Requirements for mode-locking:

- Ensemble of (localized) electron spins
- Coherence time of individual spin $T_2 >> T_R$
- Dispersion in Larmor precession frequencies



EXPERIMENT:

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